

AMENDMENTS TO THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A method for fabricating a ferroelectric memory device, comprising the steps of:

- a1) forming a lower electrode on a predetermined surface of a semiconductor substrate;
 - b1) forming a metal oxide layer over a surface of the lower electrode and a surface of the semiconductor substrate;
 - c1) forming an inter layer dielectric film over the metal oxide layer;
 - d1) performing a blanket etching for the inter layer dielectric film and the metal oxide layer in order to expose an upper surface of the lower electrode; and
 - e1) forming an opening which has a predetermined depth, wherein the opening is obtained by removing only the metal oxide layer between the inter layer dielectric film and the lower electrode through a selective etching process;
- a2) forming a ferroelectric layer on the lower electrode and the inter layer dielectric film; and
- b2) forming an upper electrode on the ferroelectric layer formed on the lower electrode.

Claim 2 (Original): The method as recited in claim 1, wherein the metal oxide layer is formed by using one of an Al_2O_3 layer, an TiO_2 layer, a TaO_2 layer, a ZrO_2 layer.

Claim 3 (Original): The method as recited in claim 1, wherein a thickness of the metal oxide layer ranges from about 1 Å to about 500 Å.

Claim 4 (Original): The method as recited in claim 1, wherein a wet etching is carried out by using a selective etching process.

Claim 5 (Original): The method as recited in claim 4, wherein the wet selective etching process is carried out by using an etching solution containing at least one selected from a group of sulfuric acid, nitric acid and phosphoric acid.

Claim 6 (Original): The method as recited in claim 5, wherein a concentration of the etching solution for the wet selective etching process ranges from about 0% to about 50%.

Claim 7 (Original): The method as recited in claim 4, wherein the wet etching process is carried out by using an etching solution containing a ammonia (NH_4OH) liquid or a hydrogen peroxide (H_2O_2) liquid.

Claim 8 (Original): The method as recited in claim 7, wherein a concentration of the etching solution containing the ammonia (NH_4OH) liquid or hydrogen peroxide (H_2O_2) liquid ranges from about 0% to 50%.

Claim 9 (Canceled)

Claim 10 (Original): The method as recited in claim 1, wherein the lower electrode is constituted sequentially with an platinum (Pt) layer, an iridium oxide (IrOx) layer and an iridium (Ir) layer.

Claim 11 (Original): The method as recited in claim 10, wherein the ferroelectric layer is constituted with one of materials of $(\text{Bi}, \text{La})_4\text{Ti}_3\text{O}_{12}$ (BLT), $\text{SrBi}_2\text{Ta}_2\text{O}_9$ (SBT), $\text{SrBi}_2(\text{Ta}_{1-x}\text{Nb}_x)_2\text{O}_9$ (SBTN), and $(\text{Pb}, \text{Zr})\text{TiO}_3$ (PZT).